

# RJK0629DPK

60V, 85A, 4.5mΩ max.  
N Channel Power MOS FET  
High-Speed Switching Use

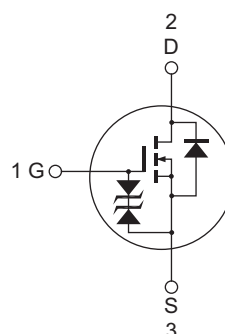
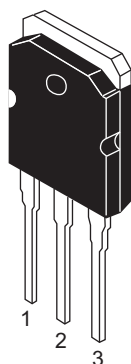
R07DS1061EJ0200  
(Previous: REJ03G1875-0100)  
Rev.2.00  
Apr 09, 2013

## Features

- $V_{DSS}$ : 60 V
- $R_{DS(on)}$ : 4.5 mΩ (Max)
- $I_D$ : 100 A

## Outline

RENESAS Package code: PRSS0004ZE-A  
(Package name: TO-3P)



1. Gate
2. Drain (Flange)
3. Source

## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Drain to source voltage	$V_{DSS}$	60	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	85	A
Drain peak current	$I_D$ (pulse) <sup>Note1</sup>	340	A
Body-drain diode reverse drain current	$I_{DR}$	85	A
Body-drain diode reverse drain peak current	$I_{DR}$ (pulse) <sup>Note1</sup>	340	A
Avalanche current	$I_{AP}$ <sup>Note2</sup>	55	A
Channel dissipation	$P_{ch}$ <sup>Note3</sup>	100	W
Channel to case thermal impedance	$\theta_{ch-c}$	1.25	$^\circ\text{C}/\text{W}$
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

- Notes: 1.  $T_{ch} \leq 150^\circ\text{C}$   
 2.  $ST_{ch} = 25^\circ\text{C}$ ,  $T_{ch} \leq 150^\circ\text{C}$ ,  $L = 100 \mu\text{H}$   
 3. Value at  $T_c = 25^\circ\text{C}$

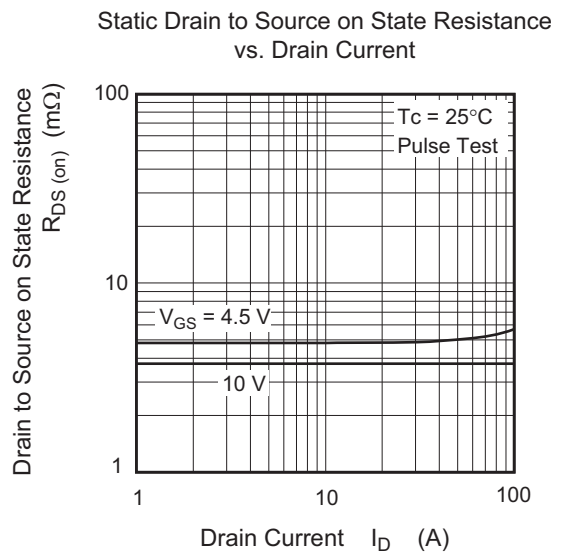
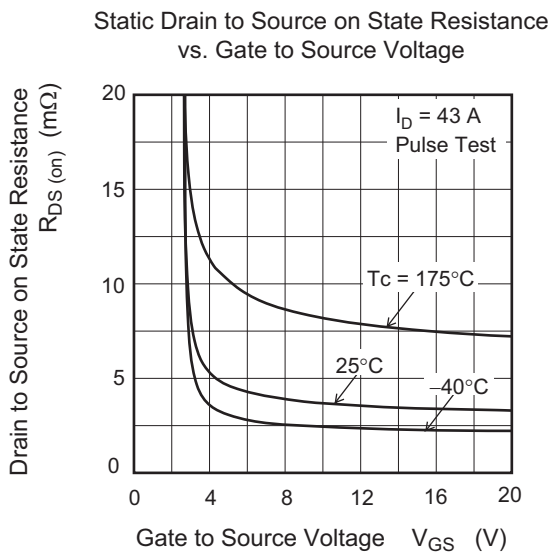
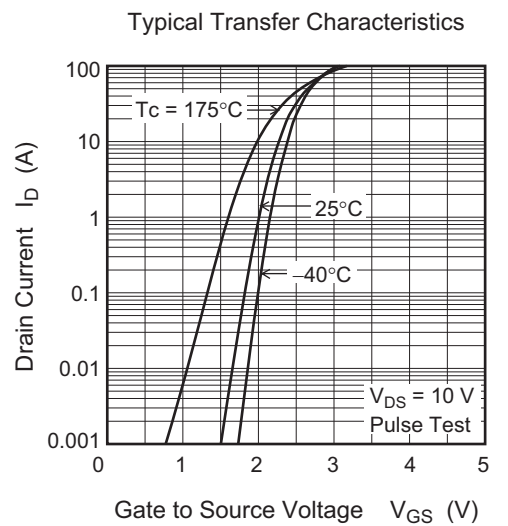
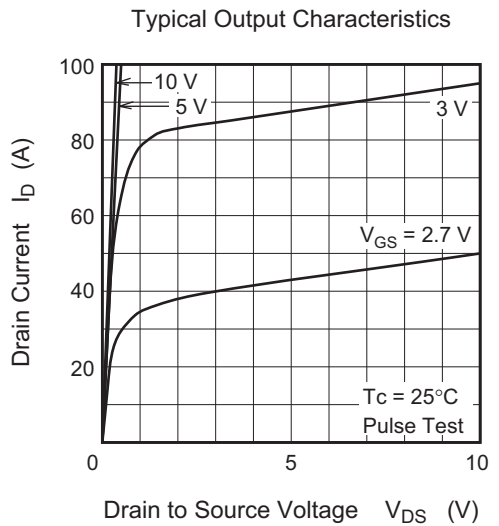
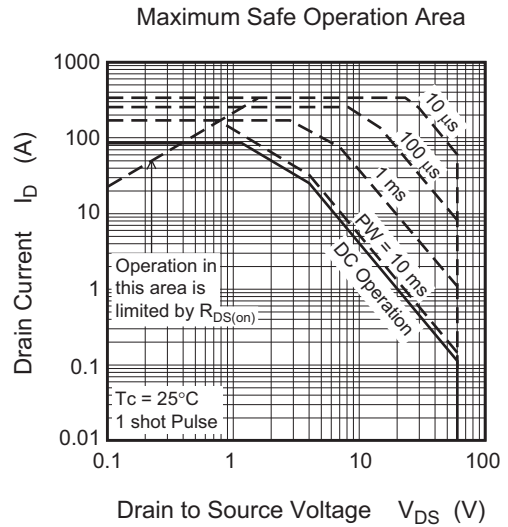
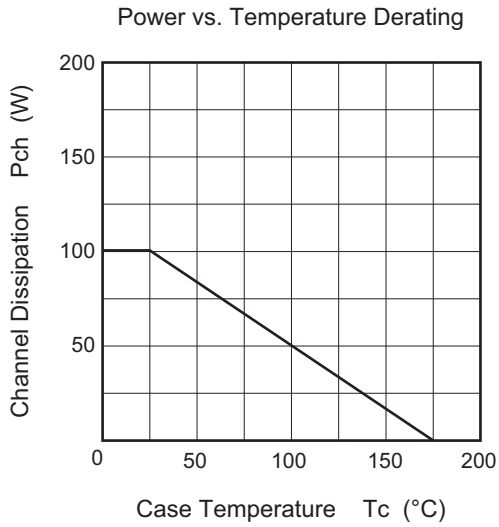
## Electrical Characteristics

(Ta = 25°C)

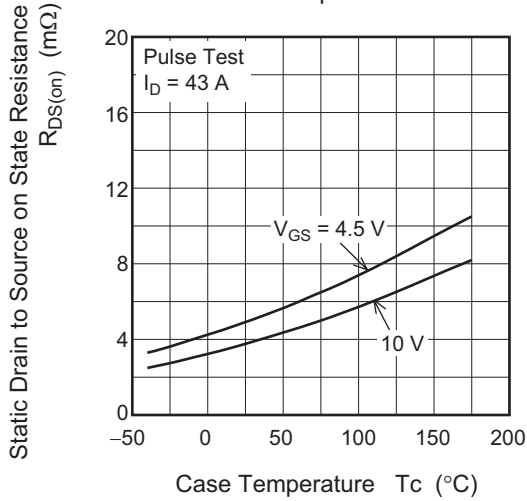
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 100 \mu A, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \mu A, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	$\mu A$	$V_{DS} = 60 V, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu A$	$V_{GS} = \pm 20 V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 mA, V_{DS} = 10 V$
Static drain to source on state voltage	$V_{DS(on)}$	—	161	194	mV	$I_D = 43A, V_{GS} = 10 V$ <sup>Note4</sup>
Static drain to source on state resistance	$R_{DS(on)}$	—	3.75	4.5	m $\Omega$	$I_D = 43A, V_{GS} = 10 V$ <sup>Note4</sup>
		—	4.9	6.6	m $\Omega$	$I_D = 43 A, V_{GS} = 4.5 V$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	4100	—	pF	$V_{DS} = 10 V, V_{GS} = 0$ $f = 1 MHz$
Output capacitance	$C_{oss}$	—	1000	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	780	—	pF	
Total gate charge	$Q_g$	—	85	—	nC	$V_{DD} = 25 V, V_{GS} = 10 V,$ $I_D = 85 A$
Gate to source charge	$Q_{gs}$	—	11	—	nC	
Gate to drain charge	$Q_{gd}$	—	25	—	nC	
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$V_{DD} = 30V, I_D = 43A,$ $V_{GS} = 10 V, R_G = 4.7 \Omega$
Rise time	$t_r$	—	40	—	ns	
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	
Fall time	$t_f$	—	40	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	0.92	1.2	V	$I_F = 85 A, V_{GS} = 0$ <sup>Note4</sup>
Body-drain diode reverse recovery time	$t_{rr}$	—	50	—	ns	$I_F = 85 A, V_{GS} = 0,$ $di_F/dt = 100 A/\mu s$

Note: 4. Pulse test

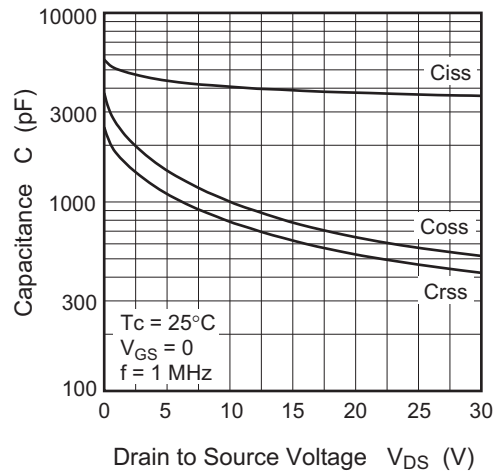
### Main Characteristics



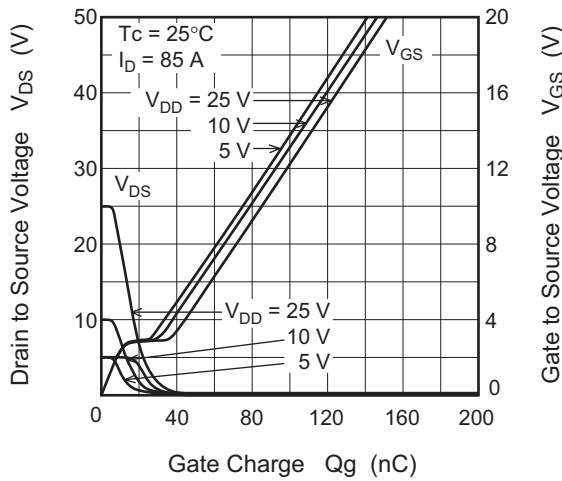
Static Drain to Source on State Resistance vs. Temperature



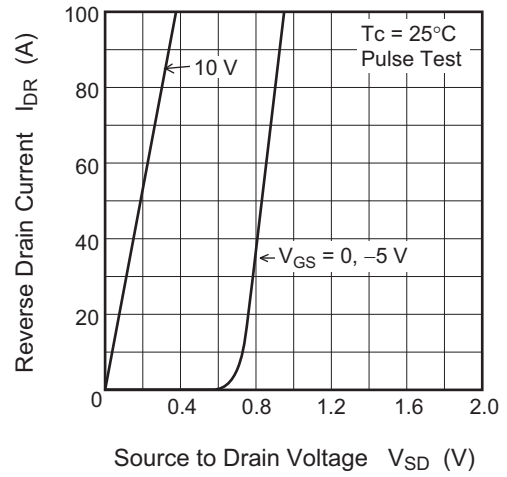
Typical Capacitance vs. Drain to Source Voltage



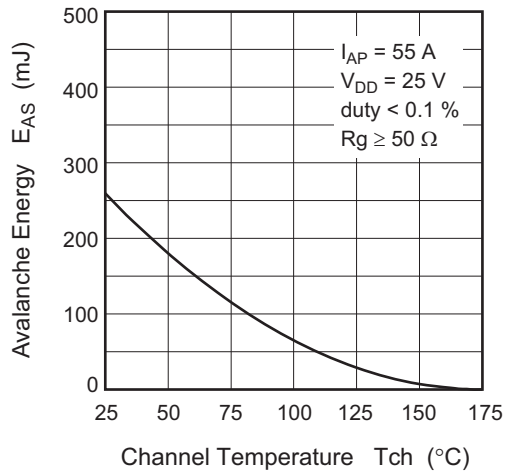
Dynamic Input Characteristics

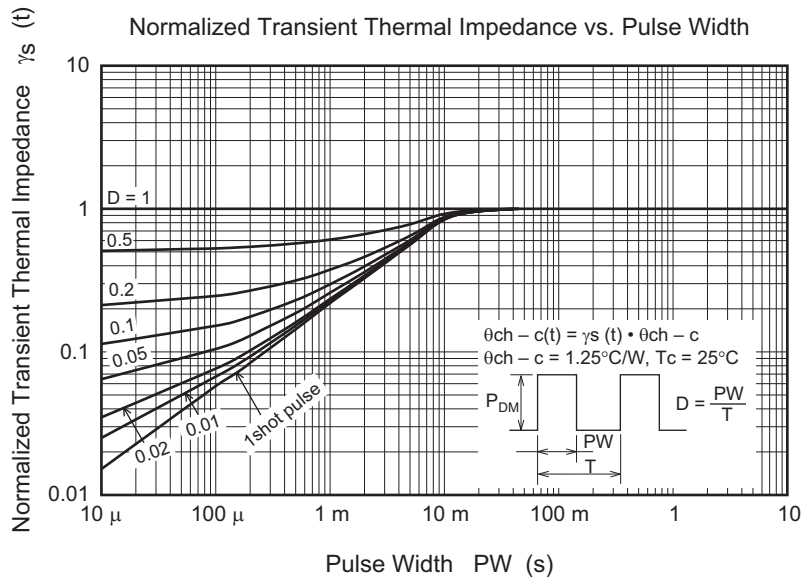


Reverse Drain Current vs. Source to Drain Voltage

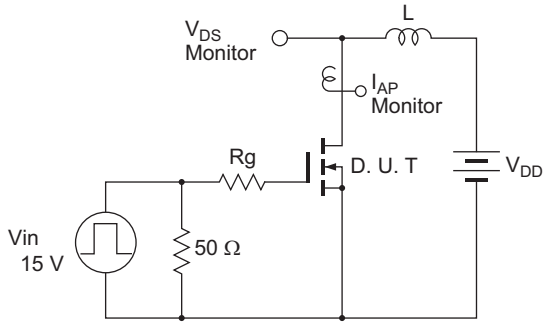


Maximum Avalanche Energy vs. Channel Temperature Derating



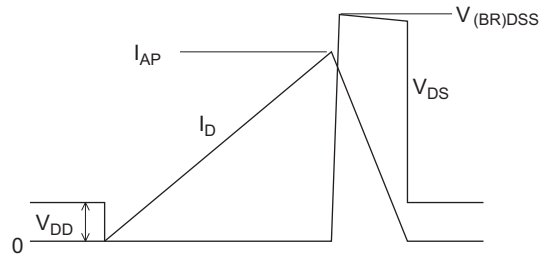


Avalanche Test Circuit

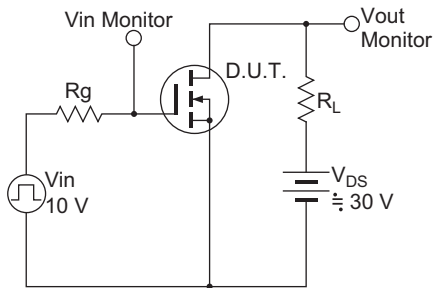


Avalanche Waveform

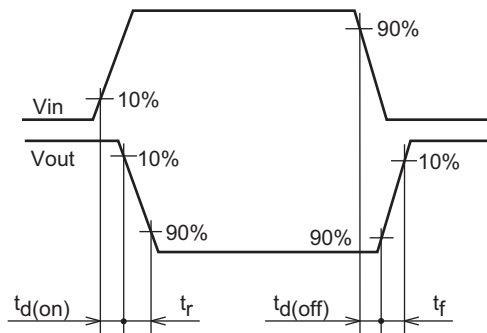
$$E_{AS} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



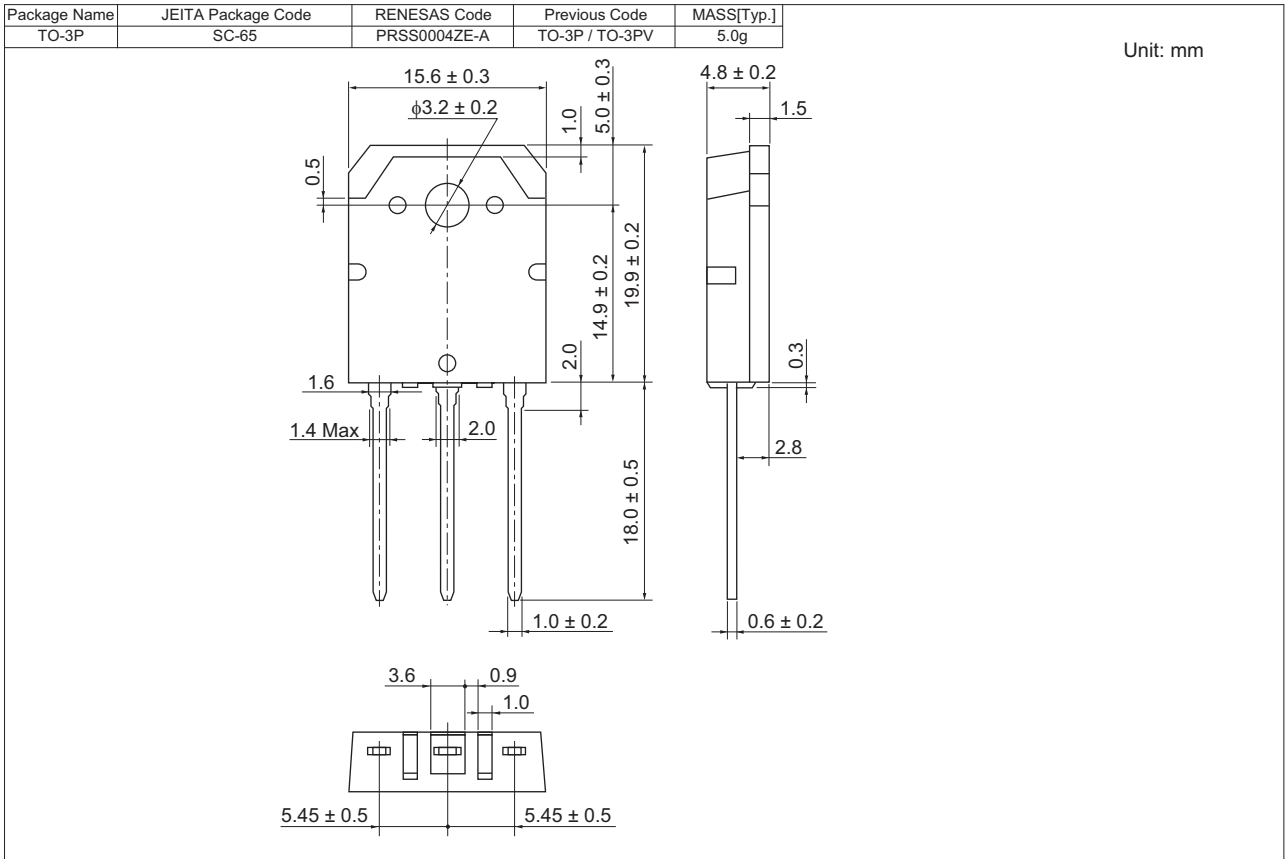
Switching Time Test Circuit



Switching Time Waveform



### Package Dimensions



### Ordering Information

Part No.	Quantity	Shipping Container
RJK0629DPK-00-T0	360 pcs	Box (Tube)

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